IN THE CLAIMS:
Please revise the claims to read as follows.

1. (Currently amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein said n-type clad layer is made thicker than each of said barrier layers and the thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and

wherein said n-type clad layer is formed of a material substantially the same as said barrier layers, ~~thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers~~ by having been formed under substantially same conditions.

2-3. (Canceled)

4. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 1, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, ~~said intermediate layer being devoid of aluminum~~.

5. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer ~~is made of~~ comprises $In_xGa_{1-x}N$, where (0

$< x < 1$).

6. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 4, wherein said intermediate layer ~~is made of~~ comprises $In_xGa_{1-x}N$, where $(0.01 \leq x \leq 0.05)$.

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7. (Currently amended) The group III nitride compound semiconductor light-emitting device of claim 1, wherein said n-type clad layer and said barrier layers ~~are formed of~~ comprise GaN.

8. (Previously presented) The semiconductor light-emitting device of claim 1, wherein a thickness of said well layer is approximately 30 Å and a thickness of said barrier layer is approximately 70 Å.

9. (Previously presented) The semiconductor light-emitting device of claim 1, further comprising:

a cap layer formed on said light-emitting layer, said cap layer being formed of a material substantially the same as said barrier layers; and

a p-type clad layer formed on and contacting said cap layer.

10. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 180 Å to 500 Å, and a light emitted comprises green light in a wavelength range of approximately 510 nm to 530 nm.

11. (Previously presented) The semiconductor light-emitting device of claim 10, wherein said thickness of said p-type clad layer is in a range of approximately 240 Å to 360 Å.

12. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 90 Å to 390 Å, and a light emitted comprises blue light in a wavelength range of approximately 460 nm to 475 nm.

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13. (Previously presented) The semiconductor light-emitting device of claim 12, wherein said thickness of said p-type clad layer is in a range of approximately 120 Å to 300 Å.

14. (Previously presented) The semiconductor light-emitting device of claim 9, wherein said p-type clad layer comprises p-type doped $Al_xGa_{1-x}N$, where x ranges from approximately 0.10 to 0.14.

15. (Currently amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,

wherein ~~said n-type clad layer is made thicker than each of said barrier layers;~~ said n-type clad layer is formed of a material substantially the same as said barrier layers, ~~said material thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers~~ by having been formed under substantially same conditions.

16. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 15, wherein said barrier layers comprise GaN.

17. (Previously presented) The group III nitride compound semiconductor light-emitting device of claim 15, further comprising:

C1 a cap layer in contact with said light-emitting layer on a side of said light-emitting layer opposite to that contacting said n-type clad layer, said cap layer being formed of a material substantially the same as said barrier layers.

18. (New) A group III nitride compound semiconductor light-emitting device (LED) having enhanced color purity, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer on a first surface;

a cap layer being in contact with said light-emitting layer on a second surface opposite said first surface,

wherein said n-type clad layer, said cap layer and each of said barrier layers are formed of a material substantially the same, by being formed under substantially the same conditions, said substantially same material thereby providing a substantially same strain on said multilayer quantum well structure that provides an enhanced color purity of light emitted from said light emitting layer.

19. (New) The LED of claim 18, wherein said substantially same material comprises GaN.

20. (New) The LED of claim 17, further comprising:

a p-clad layer on said cap layer, said p-clad layer having a thickness selected from a range of thickness that optimizes an intensity of said color.

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21. (New) The LED of claim 20, wherein said color comprises a green light in a main wavelength range of approximately 510 nm to 530 nm and said range of thickness of said p-clad layer is approximately 180 Å to 500 Å.

22. (New) The LED of claim 21, wherein said range of thickness is approximately 240 Å to 360 Å.

23. (New) The LED of claim 20, wherein said color comprises a blue light in a main wavelength range of approximately 460 nm to 475 nm and said range of thickness of said p-clad layer is approximately 90 Å to 390 Å.

24. (New) The LED of claim 23, wherein said range of thickness is approximately 120 Å to 300 Å.

25. (New) The LED of claim 20, wherein said p-type clad layer comprises a p-type doped $Al_xGa_{1-x}N$, wherein $0.10 \leq x \leq 0.14$.

26. (New) The LED of claim 18, said n-type clad layer is made thicker than each of said barrier layers and a thickness of said n-type clad layer is in a range of 100 Å to 500 Å.

27. (New) The LED of claim 19, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, said intermediate layer being devoid of aluminum.

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28. (New) The LED of claim 27, wherein said intermediate layer comprises $In_xGa_{1-x}N$, where $(0 < x < 1)$.

29. (New) The LED of claim 27, wherein $0.01 \leq x \leq 0.05$.

30. (New) A group III nitride compound semiconductor light-emitting device according to claim 5, wherein said intermediate layer comprises a material devoid of aluminum.

31. (New) A group III nitride compound semiconductor light-emitting device according to claim 7, further comprising an intermediate layer which is provided so as to be in contact with a face of said n-type clad layer opposite to said light-emitting layer, said intermediate layer comprising a material devoid of aluminum.